Abstracts

A non-quasi-static model of GaInP/AlGaAs HBT for power applications

J.P. Fraysse, D. Floriot, P. Auxemery, M. Campovecchio, R. Quere and J. Obregon. "A non-quasi-static model of GaInP/AlGaAs HBT for power applications." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 379-382.

A NonLinear (NL) model of HBT obtained from I(V) and S-parameters pulsed measurements is presented. Besides thermal effects, this model includes also two transcapacitances to take into account the Non-Quasi-Static (NQS) effects. It is shown that contrary to a Quasi-Static (QS) one, this model allows to predict accurately the behavior of the device in the whole power range as well as a broad frequency band.

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